

## 2SD2908

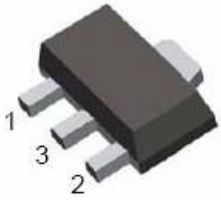
Low VCE(sat) transistor(NPN)

### Features

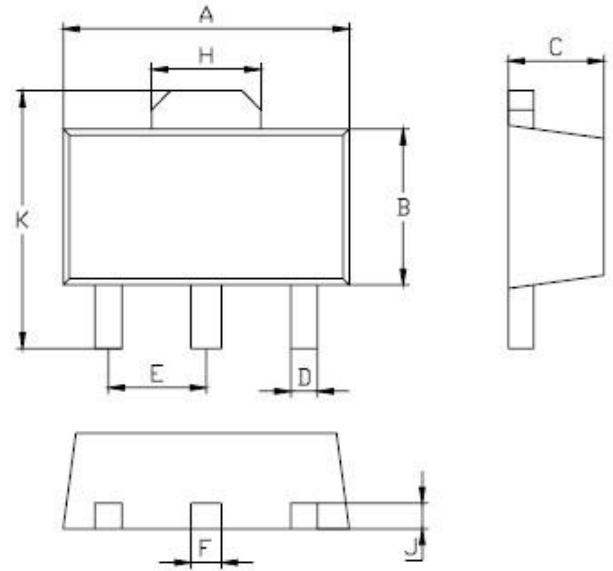
- Low VCE(sat).
- Excellent DC current gain characteristics.
- Complements the 2SB1386
- RoHS compliant package
- Case : SOT-89

### Packing & Order Information

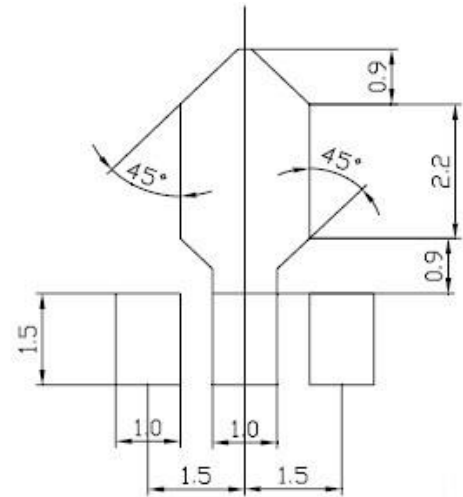
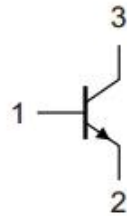
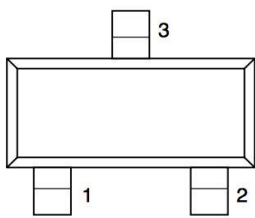
2,500/Reel



**RoHS  
COMPLIANT**



Graphic symbol



SOT-89		
Dim	Min	Max
A	4.5	4.7
B	2.3	2.7
C	1.5Typical	
D	0.35	0.55
E	1.4	1.6
F	0.4	0.6
H	1.55	1.75
J	0.4Typical	
K	4.15	4.25
All Dimensions in mm		

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### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

#### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	50	V
$V_{CEO}$	Collector-Emitter Voltage	20	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current	5	A
$P_C$	Collector Dissipation	500	mW
$T_j, T_{stg}$	Junction and Storage Temperature	-55 to +150	$^{\circ}\text{C}$

#### ELECTRICAL CHARACTERISTICS @ $T_a=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	MIN	TYP	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = 50\mu\text{A}, I_E = 0$	50			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = 1\text{ mA}, I_B = 0$	20			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = 50\mu\text{A}, I_C = 0$	6			V
$I_{CBO}$	Collector cut-off current	$V_{CB} = 40\text{ V}, I_E = 0$			0.5	$\mu\text{A}$
$I_{EBO}$	Emitter cut-off current	$V_{EB} = 5\text{ V}, I_C = 0$			0.5	$\mu\text{A}$
$h_{FE}$	DC current gain	$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$	120		390	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = 4\text{ A}, I_B = 0.1\text{ A}$		0.25	1.0	V
$f_r$	Transition frequency	$V_{CE} = 6\text{ V}, I_C = 50\text{ mA}$ $f = 100\text{ MHz}$		150		MHz
$C_{ob}$	Collector output capacitance	$V_{CB} = 20\text{ V}, I_E = 0$ $f = 1.0\text{ MHz}$		30		pF

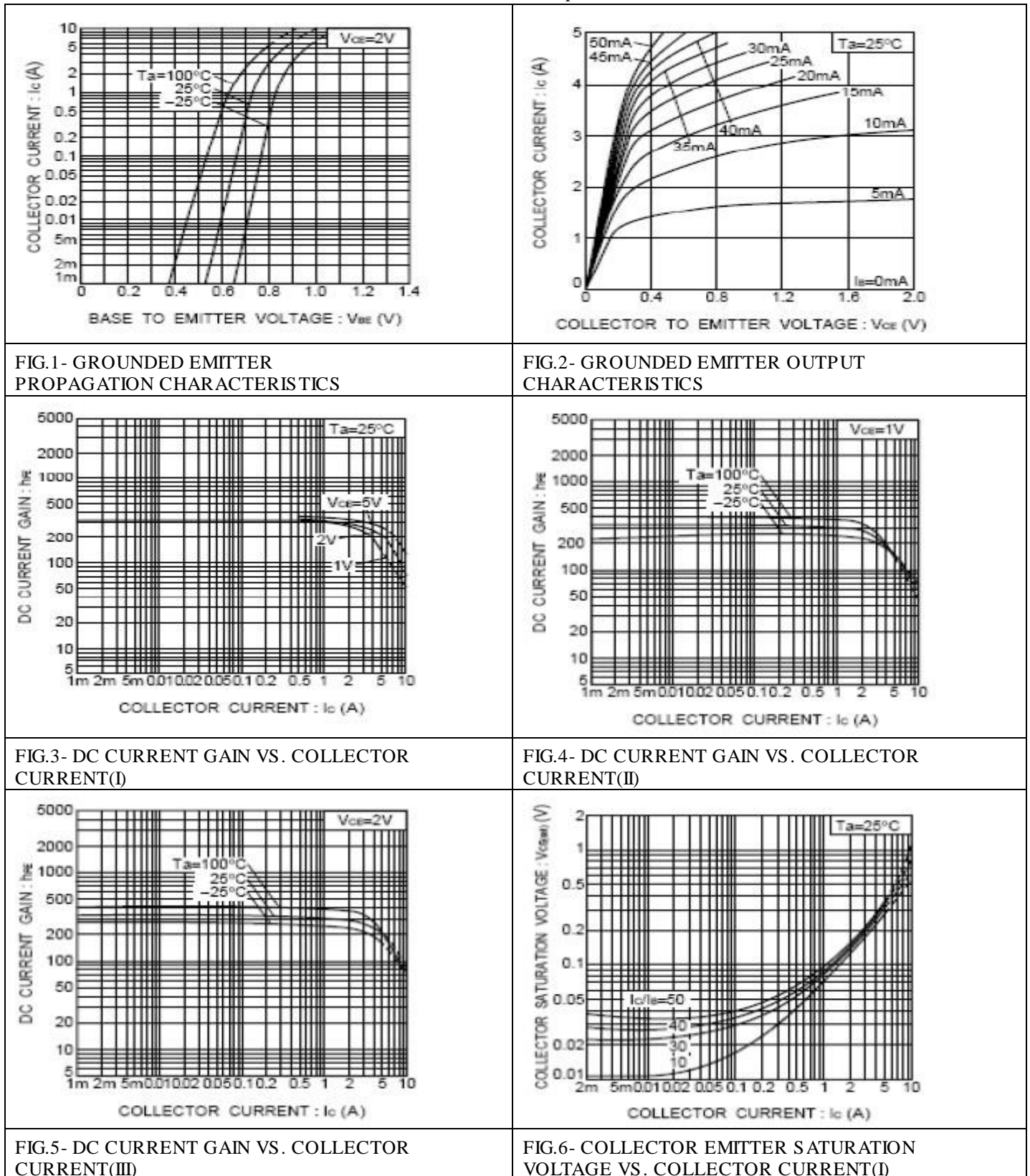
#### CLASSIFICATION OF $h_{FE}$

Marking	AHQ	AHR
Rank	Q	R
Range	120-270	180-390

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■ TYPICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified



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### Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE

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